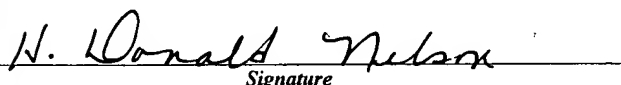



AP 2813

<b>AMENDMENT TRANSMITTAL LETTER (Large Entity)</b>				<b>Docket No.</b> D730		
Applicant(s): Shields & Ko						
Serial No. 2081325 09/200,326	Filing Date 12/9/98	Examiner T. Nguyen	Group Art Unit 2813			
Invention: <b>EAS CRITICAL TIN ARC LAYER FOR INCREASED PAD ETCH THROUGHPUT</b>				RECEIVED NOV 30 2000 TC 2800 MAIL ROOM		
<div style="border: 1px solid black; border-radius: 50%; padding: 10px; display: inline-block; transform: rotate(-15deg);"><b>OIP</b> NOV 20 2000 PATENT &amp; TRADEMARK OFFICE</div> <u>TO THE ASSISTANT COMMISSIONER FOR PATENTS:</u>						
Transmitted herewith is an amendment in the above-identified application. The fee has been calculated and is transmitted as shown below.						
<b>CLAIMS AS AMENDED</b>						
	CLAIMS REMAINING AFTER AMENDMENT	HIGHEST # PREV. PAID FOR	NUMBER EXTRA CLAIMS PRESENT	RATE	ADDITIONAL FEE	
TOTAL CLAIMS	4 -	20 =	0 x	\$18.00	\$0.00	
INDEP. CLAIMS	1 -	3 =	0 x	\$80.00	\$0.00	
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					\$0.00	
<b>TOTAL ADDITIONAL FEE FOR THIS AMENDMENT</b>					<b>\$0.00</b>	
<div><input checked="" type="checkbox"/> No additional fee is required for amendment.</div> <div><input type="checkbox"/> Please charge Deposit Account No. _____ in the amount of _____ A duplicate copy of this sheet is enclosed.</div> <div><input type="checkbox"/> A check in the amount of _____ to cover the filing fee is enclosed.</div> <div><input checked="" type="checkbox"/> The Commissioner is hereby authorized to charge payment of the following fees associated with this communication or credit any overpayment to Deposit Account No. 01-0365 A duplicate copy of this sheet is enclosed.<div><input checked="" type="checkbox"/> Any additional filing fees required under 37 C.F.R. 1.16.</div><div><input checked="" type="checkbox"/> Any patent application processing fees under 37 CFR 1.17.</div></div>						
<div> _____ Signature</div>			Dated: 11/17/00			
H. Donald Nelson, Reg. No. 28,980						
<div style="border: 1px solid black; padding: 5px; display: inline-block; transform: rotate(-15deg);"><b>RECEIVED</b> NOV 29 2000 TC 2800 MAIL ROOM</div>						
<div style="border: 1px solid black; padding: 5px;"><div>I certify that this document and fee is being deposited on 11/17/00 with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and is addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231.</div><div> _____ Signature of Person Mailing Correspondence</div><div><b>H. Donald Nelson</b> _____ Typed or Printed Name of Person Mailing Correspondence</div></div>						
cc:						



PATENT

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12/1/00IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Shields &amp; Ko

Assignee: Advanced Micro Devices, Inc.

Title: A SACRIFICIAL TiN ARC LAYER FOR INCREASED PAD ETCH THROUGHPUT

Serial No.: 09/208,325

Filed: 12/9/98

Examiner: T. Nguyen

Group Art Unit: 2813

Attorney Docket No.: D730

Anthem, Arizona  
November 17, 2000COMMISSIONER OF PATENTS AND TRADEMARKS  
Washington, D.C. 20231AMENDMENT AFTER FINAL ✓

Sir:

In response to the Examiner's Final Office Action of 9/14/00, please amend the above cited application as follows.

In the Claims

Please amend the claims as follows. In accordance with the new rules, if a claim is amended, a marked up version of the claim is included along with a clean version and, in addition, a clean set of all the claims is included.

Please amend Claims 1 & 5 as follows:

1. (Twice amended) A method of manufacturing a semiconductor device, wherein the method comprises:

forming a final layer of metal on a layer of interlayer dielectric in the semiconductor device;  
forming a layer of TiN on the final layer of metal;  
forming a first layer of photoresist on the layer of TiN;  
patterning and developing the first layer of photoresist exposing portions of the layer of TiN;  
etching holes in the layer of TiN and the final layer of metal exposing portions of the

interlayer dielectric, wherein metal structures are formed;

Law Office of  
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